## IN THE CLAIMS

Please cancel claims 9-13.

For the Examiner's convenience, a list of all claims are included below.

1. (Original) A method comprising:

selecting a dicing tape with an adhesive layer that has a thickness greater than a height of one or more bump electrodes of a wafer; and

applying the dicing tape to the wafer such that the adhesive layer conforms to the one or more bump electrodes.

- 2. (Original) The method of claim 1 wherein the wafer is a double bumped wafer.
- 3. (Original) The method of claim 2 wherein the dicing tape is applied using a mounting pressure roller wherein the adhesive layer helps to distribute a pressure applied by the mounting pressure roller.
- 4. (Original) The method of claim 3 wherein the dicing tape is a radiation sensitive tape.
- 5. (Original) The method of claim 4 wherein the bump electrodes have a height of approximately 60 microns and the adhesive layer has a thickness of approximately 130 microns.
- 6. (Original) The method of claim 5 further comprising: mounting the wafer on a support member; and

dicing the wafer using a dual-blade dicing process.

- (Original) The method of claim 6 further comprising:
   irradiating a backside of the dicing tape to reduce an adhesive strength of the adhesive layer.
- 8. (Original) The method of claim 7 wherein the adhesive strength is reduced from a preradiation adhesive strength of approximately 200 grams/25 mm<sup>2</sup> to a post-radiation adhesive strength of approximately 2 grams/25 mm<sup>2</sup>.
- 9-13 (Cancelled)
- 14. (Original) A method comprising: determining a height of one or more bump electrodes on a wafer surface; and selecting a dicing tape based upon the determined height of the one or more bump electrodes.
- 15. (Original) The method of claim 14 wherein the wafer is a double bumped wafer.
- 16. (Original) The method of claim 15 wherein selecting the dicing tape based upon the determined height of the one or more bump electrodes includes selecting a dicing tape having an adhesive layer thicker than the determined height of the one or more bump electrodes

- 17. (Original) The method of claim 16 further comprising:
- applying the dicing tape to the wafer such that the adhesive layer conforms to the one or more bump electrodes.
- 18. (Original) The method of claim 17 wherein the dicing tape is applied using a mounting pressure roller wherein the adhesive layer helps to distribute a pressure applied by the mounting pressure roller.
- 19. (Original) The method of claim 14 wherein the dicing tape is a radiation sensitive tape having a pre-radiation adhesive strength of approximately 200 grams/25 mm<sup>2</sup>, and a post-radiation adhesive strength of approximately 2 grams/25 mm<sup>2</sup>.
- 20. (Original) The method of claim 14 wherein the bump electrodes have a height of approximately 60 microns and the adhesive layer has a thickness of approximately 130 microns.
- 21. (Original) The method of claim 20 further comprising:
  mounting the wafer on a support member; and
  dicing the wafer using a dual-blade dicing process.
- 22. (Original) The method of claim 21 further comprising: irradiating a backside of the dicing tape to reduce an adhesive strength of the adhesive layer.

23. (Original) A method comprising:

applying an adhesive to a wafer surface, the wafer surface having one or more bump electrodes formed thereon, the adhesive covering the one or more bump electrodes to form an adhesive layer; and

applying a backing film to the adhesive layer.

- 24. (Original) The method of claim 23 wherein the wafer is a double bumped wafer.
- 25. (Original) The method of claim 23 wherein the backing film is applied using a mounting pressure roller wherein the adhesive layer helps to distribute a pressure applied by the mounting pressure roller.
- 26. (Original) The method of claim 25 wherein the bump electrodes have a height of approximately 60 microns and the adhesive layer has a thickness of approximately 130 microns.
- 27. (Original) The method of claim 23 further comprising:
  mounting the wafer on a support member; and
  dicing the wafer using a dual-blade dicing process.